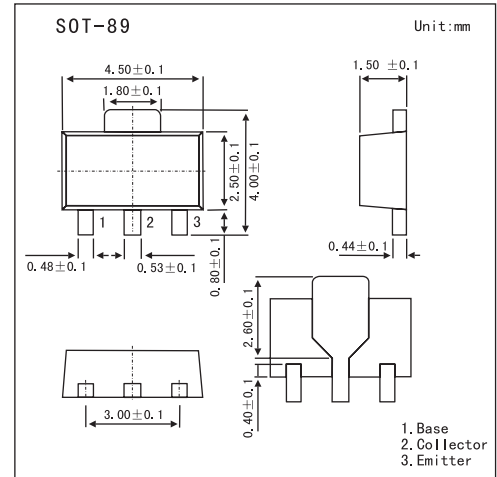


NPN Silicon Epitaxia

2SC3617



Features

- World standard miniature package.
- High hFE hFE=800 to 1600.

Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	15	V
Collector current	I _C	300	mA
Collector current (Pulse)*	I _{CP}	500	mA
Total power dissipation	P _T	2.0	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10ms, duty cycle ≤ 50%.

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	V _{CB} = 50V, I _E = 0			100	nA
Emitter cutoff current	I _{EB0}	V _{EB} = 10V, I _C = 0			100	nA
DC current gain *	h _{FE}	V _{CE} = 5.0V, I _C = 100mA	800		3200	
		V _{CE} = 5.0V, I _C = 300mA	640			
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = 100mA, I _B = 1.0mA		0.12	0.13	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C = 100mA, I _B = 1.0mA		0.7	1.2	V
Gain bandwidth product	f _T	V _{CE} = 5.0V, I _E = -50mA	150	220		MHz
Output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1.0MHz		8.0		pF

*. PW ≤ 350μs, duty cycle ≤ 2%

hFE Classification

Marking	TM	TL	TK
hFE	800~1600	1200~2400	2000~3200